## **CLAIM AMENDMENTS**

1. (currently amended) An on-chip inductor consisting of:
a <u>first</u> dielectric layer;
a conductive winding on the <u>first</u> dielectric layer;
a second dielectric layer having a major surface parallel to a major surface of the first dielectric layer;
a P-well having a major surface parallel to [[a]] the major surface of the first dielectric layer; and
a substrate having a major surface parallel to the major surface of the <u>first</u> dielectric layer.
2. (currently amended) The on-chip inductor of claim 1 further consists of An on-chip inductor consisting of:
a <u>first</u> dielectric layer;
a conductive winding on the <u>first</u> dielectric layer;
a second dielectric layer having a major surface parallel to a major surface of the first dielectric layer;
a P-well having a major surface parallel to [[a]] the major surface of the first dielectric layer;

a field oxide having a major surface that is juxtaposed to the major surface of the P-well; and

a substrate having a major surface parallel to the major surface of the first dielectric layer.

3. (previously presented) The on-chip inductor of claim 1 wherein:

the conductive winding is a spiral winding.

4 - 8. (canceled).

- 9. (currently amended) An on-chip inductor consisting of:
- a first dielectric layer;

a conductive winding on the at least one first dielectric layer;

a second dielectric layer having a major surface parallel to a major surface of the first dielectric layer;

a field oxide layer having a major surface parallel to [[a]]  $\underline{\text{the}}$  major surface of the  $\underline{\text{first}}$  dielectric layer; and

a substrate having a major surface parallel to the major surface of the <u>first</u> dielectric layer.

10 -30. (canceled)